

## isc Silicon NPN Power Transistor

## BUT11AF

### DESCRIPTION

- High Voltage
- High Speed Switching
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### APPLICATIONS

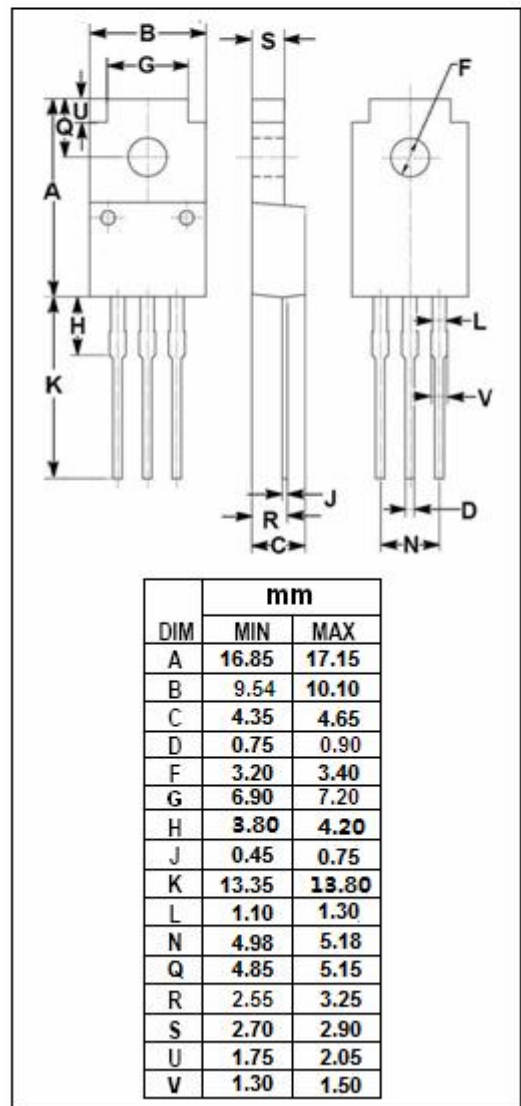
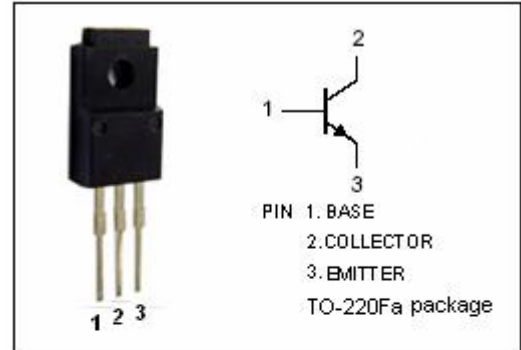
- Converters
- Inverters
- Switching regulators
- Motor control systems

### ABSOLUTE MAXIMUM RATINGS (T<sub>a</sub>=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	Collector-Base Voltage	1000	V
V <sub>CEO</sub>	Collector-Emitter Voltage	450	V
V <sub>EBO</sub>	Emitter-Base Voltage	9	V
I <sub>C</sub>	Collector Current-Continuous	5	A
I <sub>CM</sub>	Collector Current-Peak	10	A
I <sub>B</sub>	Base Current	2	A
I <sub>BM</sub>	Base Current-Peak	4	A
P <sub>C</sub>	Collector Power Dissipation @T <sub>C</sub> =25°C	40	W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature Range	-65~150	°C

### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th j-c</sub>	Thermal Resistance, Junction to Case	3.125	K/W



**isc Silicon NPN Power Transistor****BUT11AF****ELECTRICAL CHARACTERISTICS****T<sub>c</sub>=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 50mA; I <sub>B</sub> = 0	450			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 2.5A; I <sub>B</sub> = 0.5A			1.5	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 2.5A; I <sub>B</sub> = 0.5A			1.3	V
I <sub>CES</sub>	Collector Cutoff Current	V <sub>CE</sub> = 1000V ; V <sub>BE</sub> = 0			1.0	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 9V; I <sub>C</sub> = 0			10	mA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 5mA ; V <sub>CE</sub> = 5V	10		35	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 0.5A ; V <sub>CE</sub> = 5V	10		35	

Switching Times; Resistive Load

t <sub>on</sub>	Turn-on Time				1.0	μs
t <sub>s</sub>	Storage Time	I <sub>C</sub> = 2.5A; I <sub>B1</sub> = -I <sub>B2</sub> = 0.5A V <sub>CC</sub> = 250V; R <sub>L</sub> = 100Ω			4.0	μs
t <sub>f</sub>	Fall Time				0.8	μs

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